

SSM6L11TU

High Speed Switching Applications

- Optimum for high-density mounting in small packages
- Low on-resistance Q1: $R_{on} = 395\text{m}\Omega$ (max) (@ $V_{GS} = 1.8\text{ V}$)
Q2: $R_{on} = 430\text{m}\Omega$ (max) (@ $V_{GS} = -2.5\text{ V}$)

Q1 Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	20	V
Gate-Source voltage		V_{GSS}	± 12	V
Drain current	DC	I_D	0.5	A
	Pulse	I_{DP}	1.5	

Q2 Maximum Ratings ($T_a = 25^\circ\text{C}$)

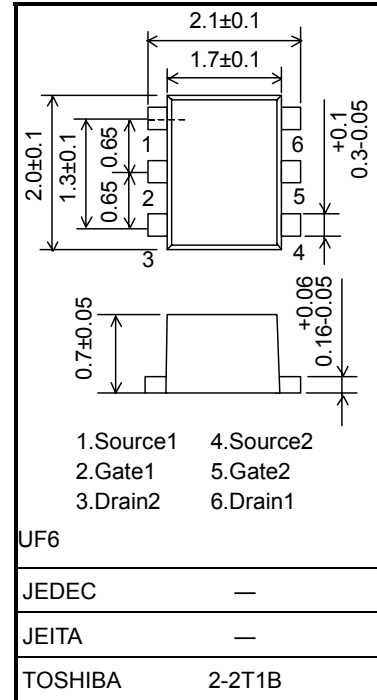
Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	-20	V
Gate-Source voltage		V_{GSS}	± 12	V
Drain current	DC	I_D	-0.5	A
	Pulse	I_{DP}	-1.5	

Maximum Ratings (Q1,Q2 Common)($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Drain power dissipation	P_D (Note1)	500	mW
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

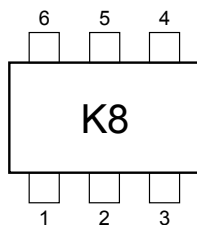
Note1: Mounted on FR4 board. (total dissipation)
(25.4 mm $\times$ 25.4 mm $\times$ 1.6 t, Cu Pad: 645 mm²)

Unit: mm

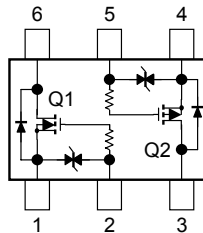


Weight: 7.0 mg (typ.)

Marking



Equivalent Circuit (top view)



Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

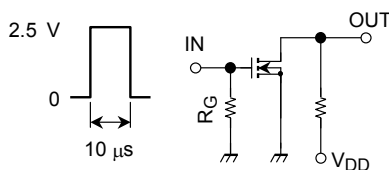
Q1 Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$	—	—	± 1	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1 mA, V_{GS} = 0$	20	—	—	V
	$V_{(BR)DSX}$	$I_D = 1 mA, V_{GS} = -12 V$	10	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = 20 V, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 3 V, I_D = 0.1 mA$	0.5	—	1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 V, I_D = 0.25 A$ (Note2)	1.2	2.4	—	S
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = 0.25 A, V_{GS} = 4.0 V$ (Note2)	—	125	145	m Ω
		$I_D = 0.25 A, V_{GS} = 2.5 V$ (Note2)	—	150	190	
		$I_D = 0.25 A, V_{GS} = 1.8 V$ (Note2)	—	200	395	
Input capacitance	C_{iss}	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	—	268	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	—	34	—	pF
Output capacitance	C_{oss}	$V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz$	—	44	—	pF
Switching time	Turn-on time	$V_{DD} = 10 V, I_D = 0.25 A,$ $V_{GS} = 0 \sim 2.5 V, R_G = 4.7 \Omega$	—	11	—	ns
	Turn-off time		—	15	—	

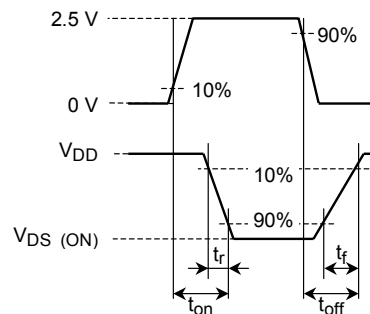
Note2: Pulse test

Switching Time Test Circuit

(a) Test Circuit



$V_{DD} = 10 V$
 $R_G = 4.7 \Omega$
 $D.U. \leq 1\%$
 $V_{IN}: t_r, t_f < 5 ns$
 Common Source
 $T_a = 25^\circ C$

(b) V_{IN} (c) V_{OUT}

Precaution

V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 100 \mu A$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} and $V_{GS(off)}$ requires a lower voltage than V_{th} .

(The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$)

Please take this into consideration when using the device. The V_{GS} recommended voltage for turning on this product is 1.8 V or higher.

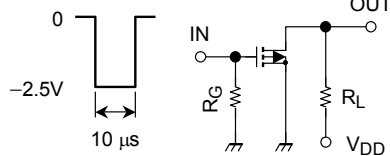
Q2 Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$	—	—	± 1	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1 mA, V_{GS} = 0$	-20	—	—	V
	$V_{(BR)DSX}$	$I_D = -1 mA, V_{GS} = +12 V$	-8	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = -20 V, V_{GS} = 0$	—	—	-1	μA
Gate threshold voltage	V_{th}	$V_{DS} = -3 V, I_D = -0.1 mA$	-0.5	—	-1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3 V, I_D = -0.25 A$ (Note3)	0.65	1.3	—	S
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = -0.25 A, V_{GS} = -4 V$ (Note3)	—	210	260	$m\Omega$
		$I_D = -0.25 A, V_{GS} = -2.5 V$ (Note3)	—	310	430	
Input capacitance	C_{iss}	$V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz$	—	218	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz$	—	42	—	pF
Output capacitance	C_{oss}	$V_{DS} = -10 V, V_{GS} = 0, f = 1 MHz$	—	52	—	pF
Switching time	Turn-on time	$V_{DD} = -10 V, I_D = -0.25 A,$ $V_{GS} = 0 \sim -2.5 V, R_G = 4.7 \Omega$	—	16	—	ns
	Turn-off time		—	15	—	

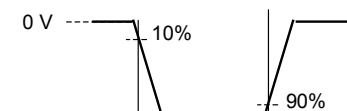
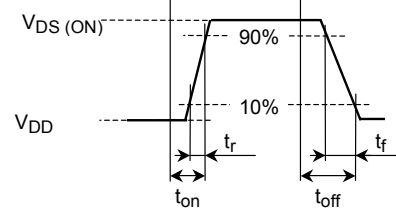
Note3: Pulse test

Switching Time Test Circuit

(a) Test circuit



$V_{DD} = -10 V$
 $R_G = 4.7 \Omega$
 $D.U. \leq 1\%$
 $V_{IN}: t_r, t_f < 5 ns$
 Common Source
 $T_a = 25^\circ C$

(b) V_{IN} (c) V_{OUT} 

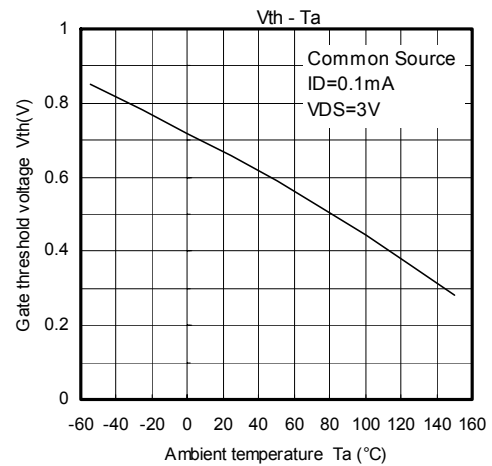
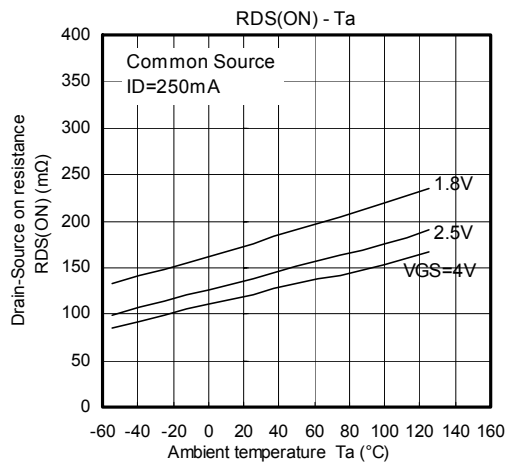
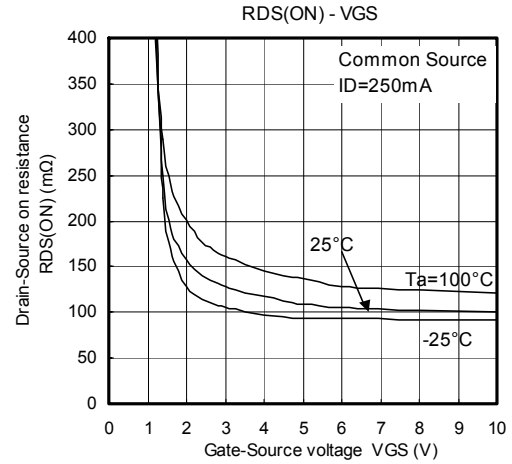
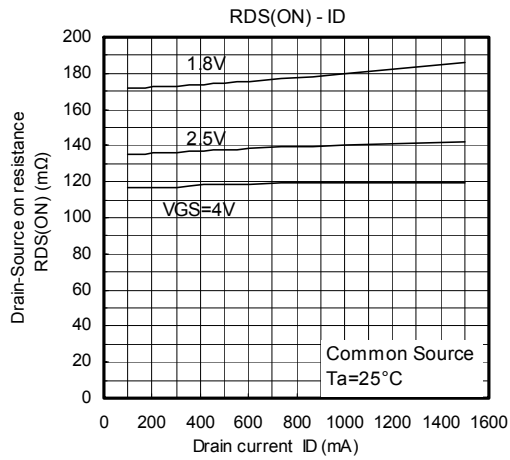
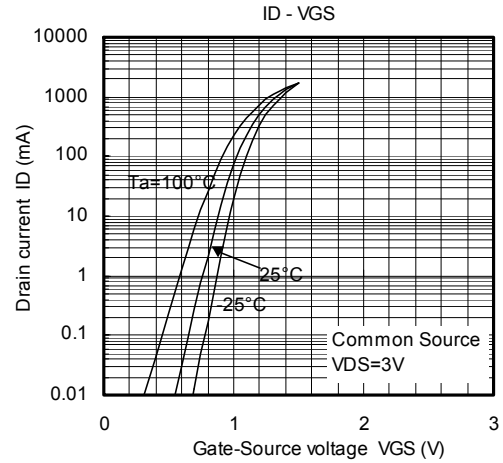
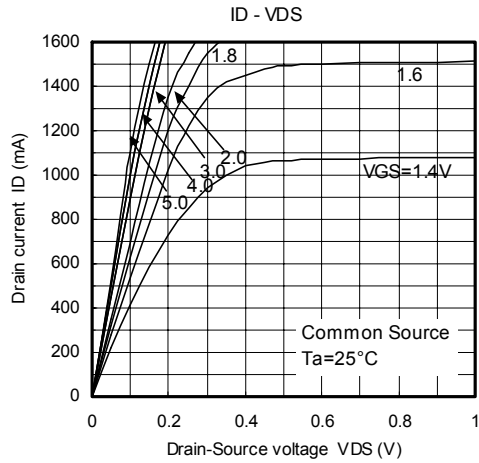
Precaution

V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = -100 \mu A$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} and $V_{GS(off)}$ requires a lower voltage than V_{th} .

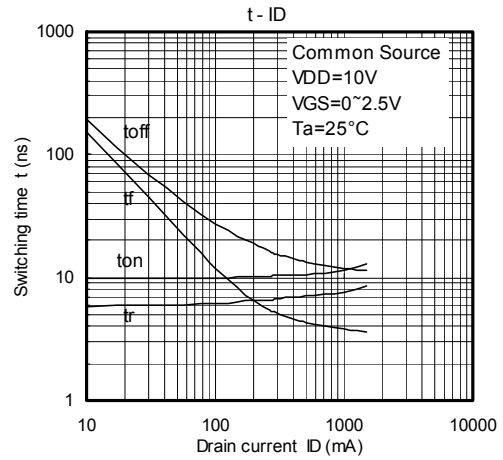
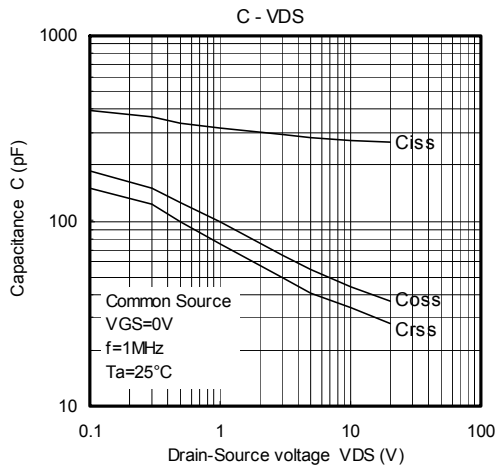
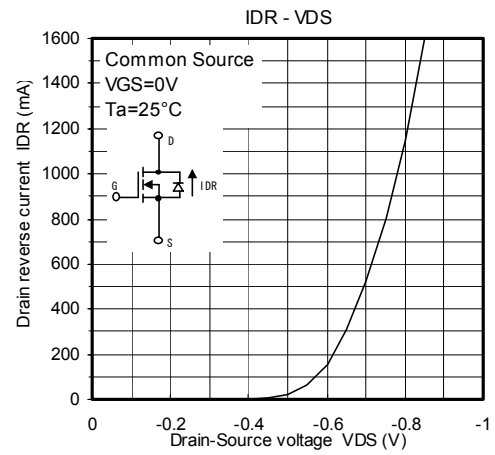
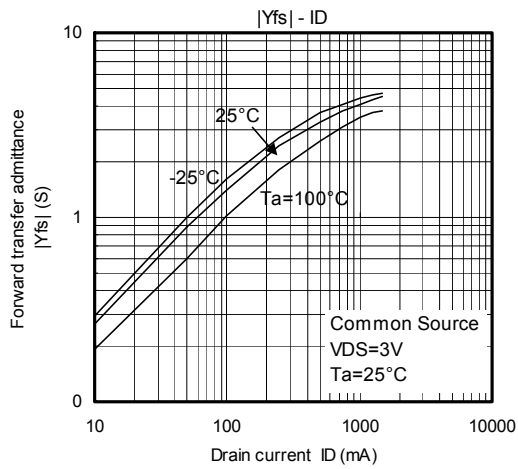
(The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$)

Please take this into consideration when using the device. The V_{GS} recommended voltage for turning on this product is -2.5V or higher.

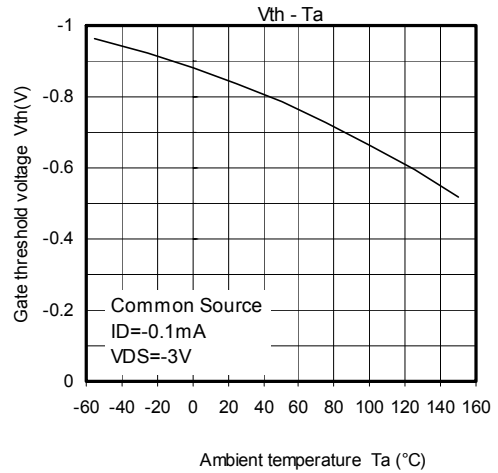
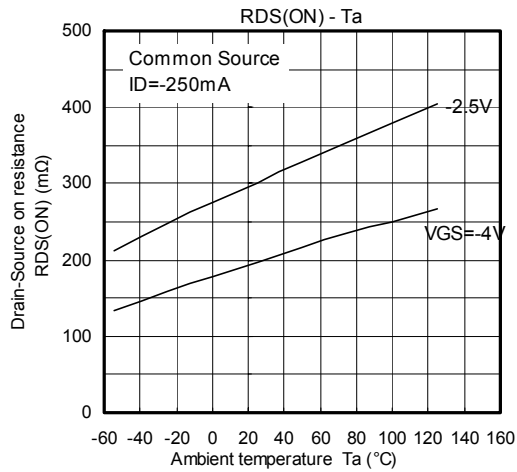
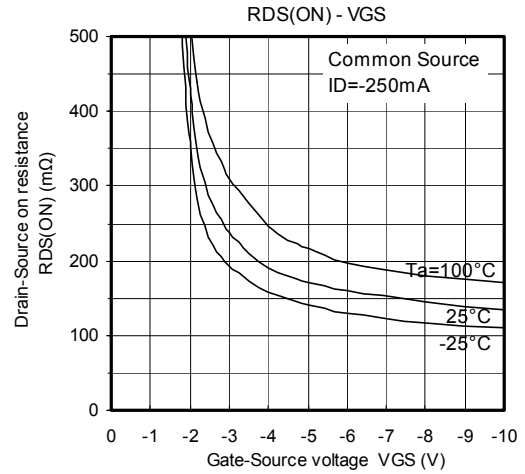
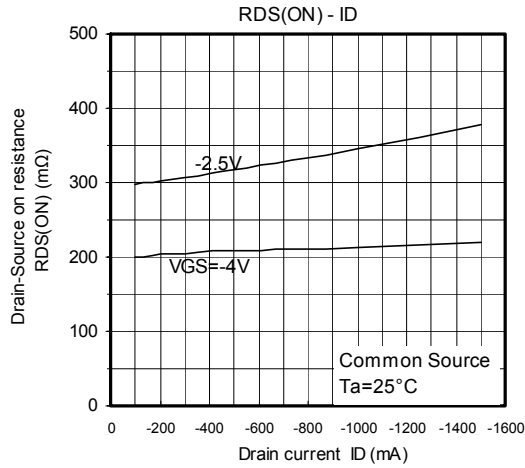
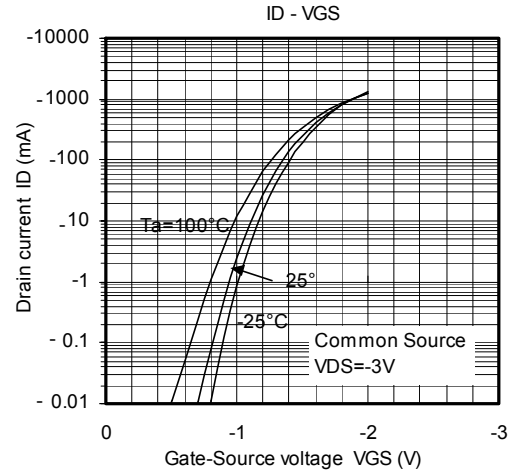
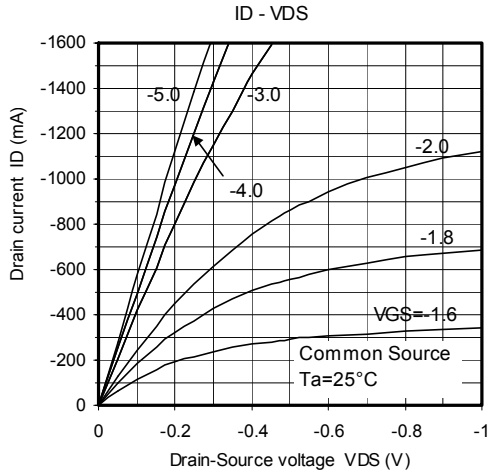
Q1(Nch MOS FET)



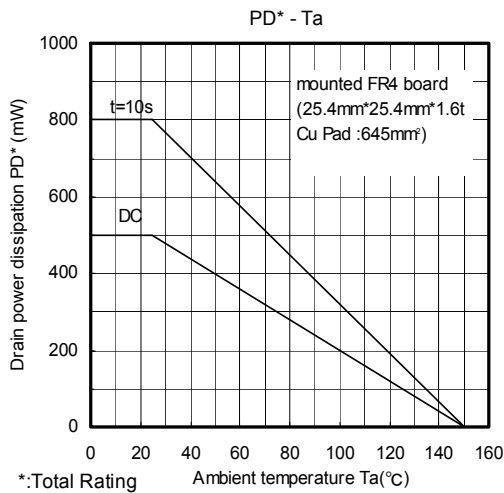
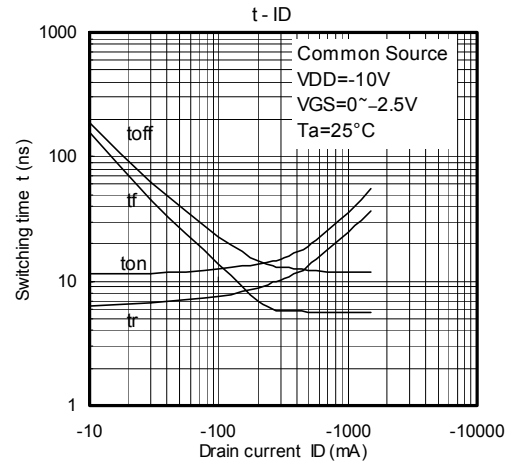
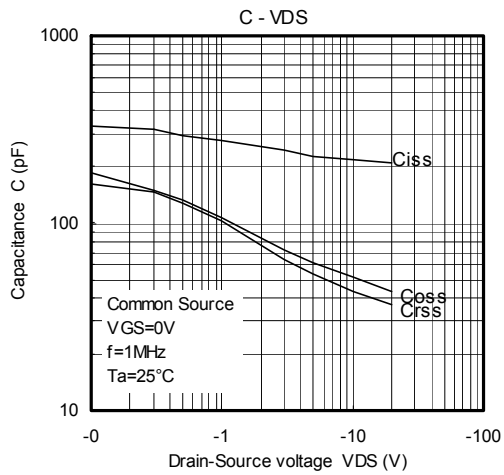
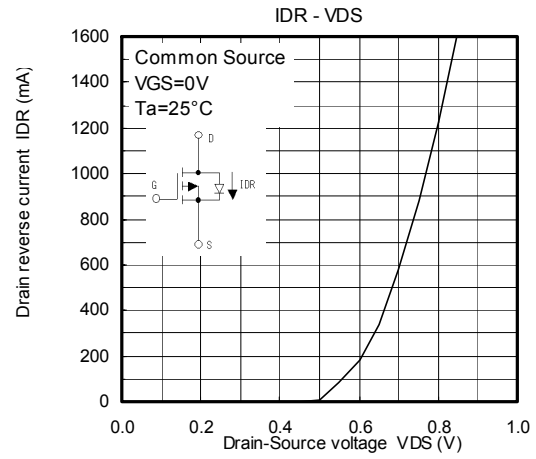
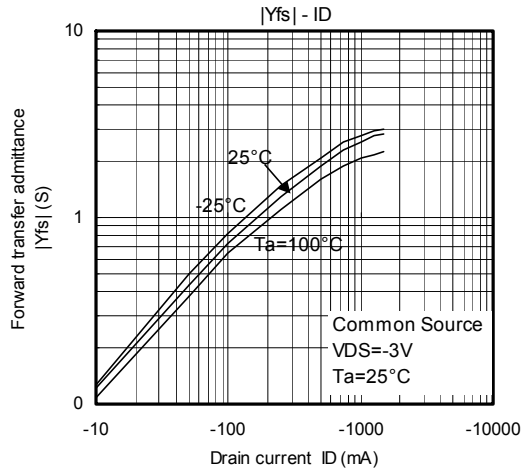
Q1(Nch MOS FET)

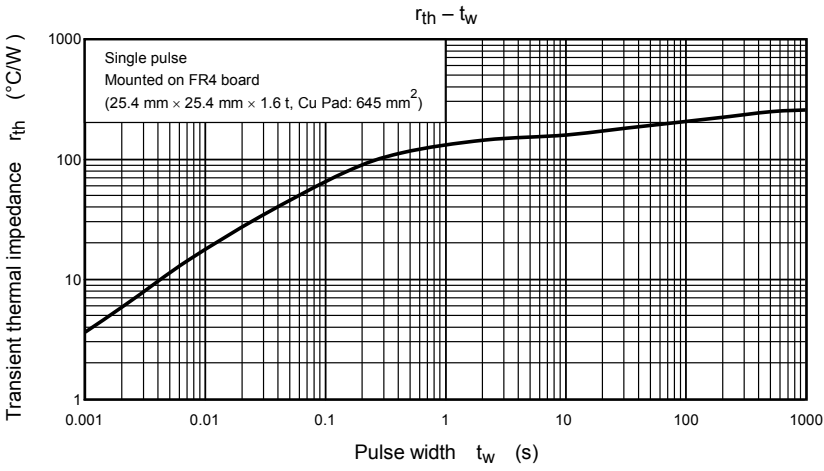


Q2(Pch MOS FET)



Q2(Pch MOS FET)





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